

Supporting Information

NiS₂ nanoboxes wrapped in carbon with a core-shell structure for high-performance sodium storage

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Experimental section

Synthesis of Ni-based metal organic compound (Ni-MOC) nanoparticles

First, 1.152 g of nickel (II) acetate tetrahydrate and 3.15 g of polyvinylpyrrolidone (PVP, with a molecular weight of 58,000) were added to 180 ml of anhydrous ethanol at room temperature. The mixture was then stirred for 30 minutes to ensure complete dissolution. Subsequently, the solution was transferred to an oil bath at a temperature of 85 °C and stirred for 24 hours. After that, the green precipitate of Ni-MOC was isolated through centrifugation. The obtained precipitate was collected, washed thrice with ethanol, and subsequently dried at 60 °C.

Synthesis of Ni-MOC@PAN

412 mg of as-synthesized Ni-MOC powder was dispersed in 2.5 ml of dimethylformamide (DMF) solvent by ultrasonic treatment. Then, 206 mg of Polyacrylonitrile (PAN, with a molecular

weight of 150,000) was added to the solution and stirred at room temperature for 48 hours to ensure complete dissolution. During the electrospinning process, the distance between the nozzle and the aluminum foil was kept at 12 cm, and the nozzle was driven by a 13 kV voltage at a stable filamentation speed of 0.03 mm min⁻¹, resulting in the formation of Ni-MOC@PAN. Under the same experimental conditions, the ratio of Ni-MOC-to-PAN was varied, specifically set to 1:1 and 3:1 respectively.

Synthesis of NiS₂@N-C

The as-obtained Ni-MOC@PAN composite was placed downstream of a ceramic boat, and a specific amount of sulfur powder (mass ratio between Ni-MOC@PAN: sulfur powder = 1:5) was added upstream. The ceramic boat was then positioned in a tube furnace and heated in an argon atmosphere at a rate of 1°C min⁻¹ until reaching 450 °C, and maintained for 3 hr to facilitate the sulfidation reaction. The resulting product obtained was the NiS₂@N-C composite. Under the same experimental conditions, the sulfidation temperatures were altered, being set at 600 °C and 750 °C, respectively.

Synthesis of Pure NiS₂

Under the same experimental conditions, Ni-MOC was directly sulfurized to produce pure NiS₂.

Synthesis of N-C

In the Ni-MOC@PAN synthesis conditions mentioned above, pure PAN fibers were obtained without the addition of Ni-MOC powder, which were then carbonized using the above conditions.

Material Characterization

X-ray diffractometer (XRD, Malvern Panalytical) was used to analyze the chemical phase of the samples. The morphological and microstructural examinations were carried out using scanning electron microscopy (SEM, Phenom Pharos) and transmission electron microscopy (TEM, JEM2010F). The chemical state of the samples was determined by X-ray photoelectron spectroscopy (XPS, Thermo Scientific K-Alpha). The carbon content in the samples was analyzed using a thermogravimetric analyzer (TGA, NETZSCH STA 449F5), and surface texture of the samples were measured by the nitrogen adsorption/desorption isotherms using a surface analyzer (Kubo-X1000).

Electrochemical measurement

For the fabrication of the electrodes, the active material, Super P conductive agent, and PVDF binder were mixed in a mass ratio of 7:2:1 and stirred evenly. The mixed slurry was then spread

evenly on a copper foil and dried overnight in a vacuum environment at 80 °C. The half-cell was assembled using a CR2025 coin cell casing within an argon-filled glove box, with water and oxygen levels maintained below 1 ppm. Metallic sodium and glass fiber (Whatman) were used as the anode and separator, respectively, with 1 M NaPF₆ in dimethyl ether (DME) as the electrolyte. The mass loading of active material in each electrode ranged from 0.8 to 1.2 mg cm⁻². Charge-discharge tests and CV analysis were carried out within a voltage range of 0.01-3.0 V (vs. Na/Na⁺) at varying current densities and different scan rates, respectively. Furthermore, EIS measurements were performed across a frequency range of 0.01-10⁵ Hz using a Bio-Logic SP-150 electrochemical workstation.

Theoretical Calculation

Utilizing Density Functional Theory (DFT) in conjunction with the Vienna Ab initio Simulation Package (VASP), developed at the University of Vienna, Austria, first-principles calculations were performed. Within the framework of the Generalized Gradient Approximation (GGA), the Perdew-Burke-Ernzerhof (PBE) approach was employed to elucidate the interactions among electrons. To address the strong electron interactions in the 3d orbitals of transition metals, we introduced the DFT+U method in our calculations and performed spin-polarized treatment. The U-J difference for nickel (Ni) was set to 6.4 electron volts. The (200) crystal plane of cubic NiS₂ along with a single-layer carbon network was selected to construct a heterostructure model. To eliminate the untrue interaction effect, we set a vacuum layer thickness of 15 angstroms in the model. The adsorption energy of Na⁺ (ΔE_{ads}) was defined as:

$$E_{\text{ads}} = E_{\text{total}} - E_{\text{base}} - E_{\text{Na}}$$

where E_{total} is the total energy of the substrate adsorbed with Na⁺, while E_{base} and E_{Na} are the energy of the substrate and Na⁺, respectively.

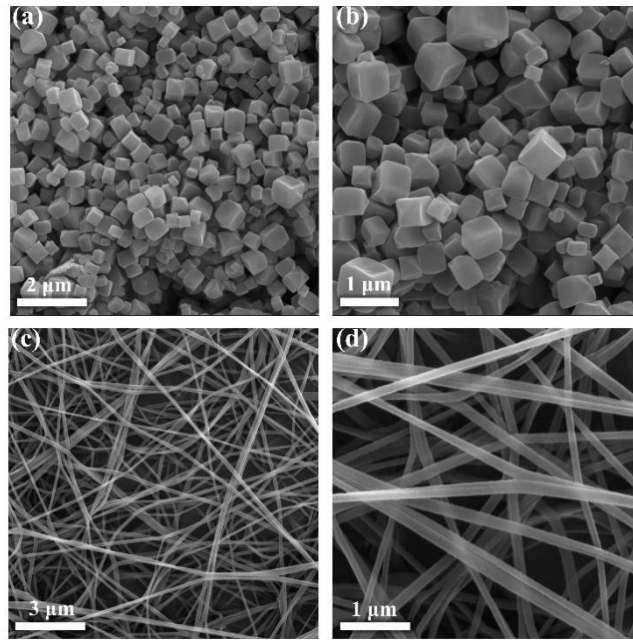


Figure S1. SEM images of (a-b) Ni-MOC and (c-d) pure PAN fibers.

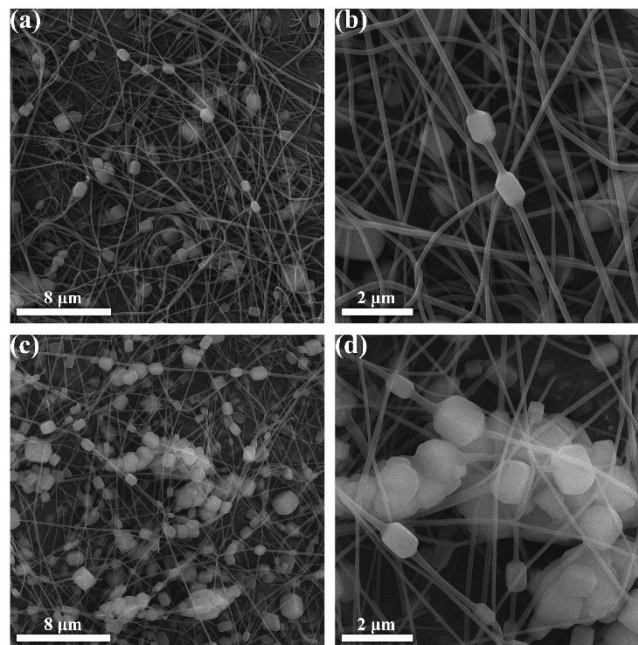


Figure S2. SEM images of samples prepared with different Ni-MOC-to-PAN ratio: (a-b) 1:1 and (c-d) 3:1.

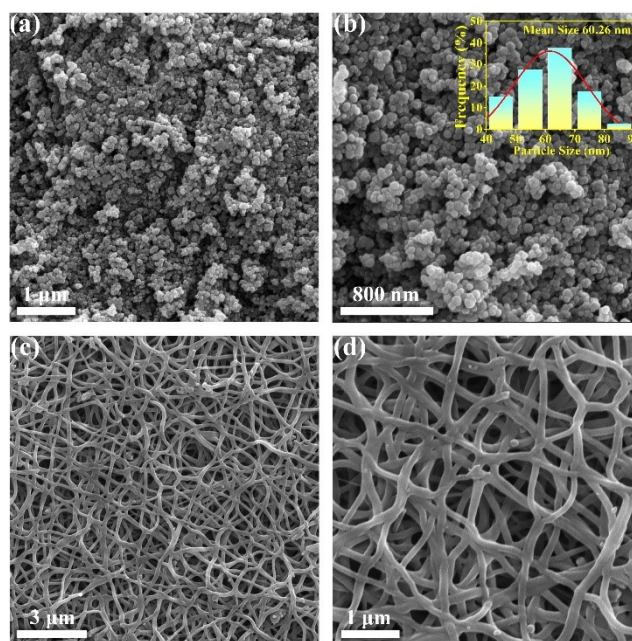


Figure S3. (a-b) SEM images of Pure NiS₂ and the size distribution diagrams of pure NiS₂ nanoparticles. (c-d) SEM images of N-C after sulfurization.

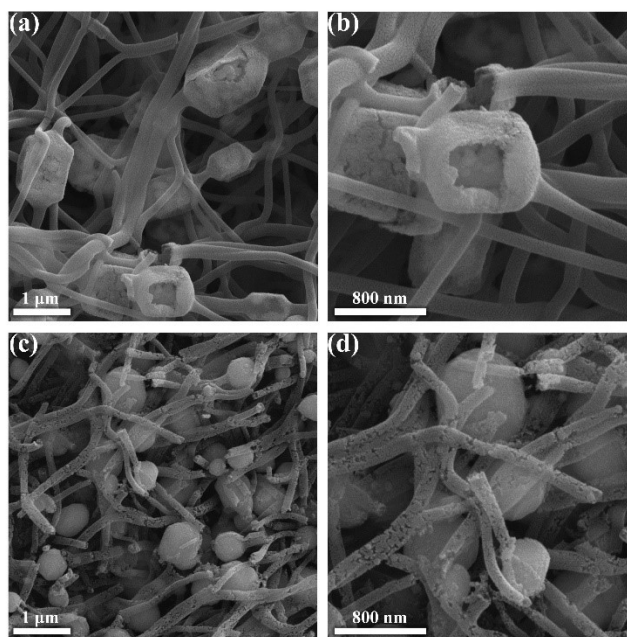


Figure S4. SEM images of the sample prepared at different carbonization temperatures: (a-b) 600 °C and (c-d) 750 °C.

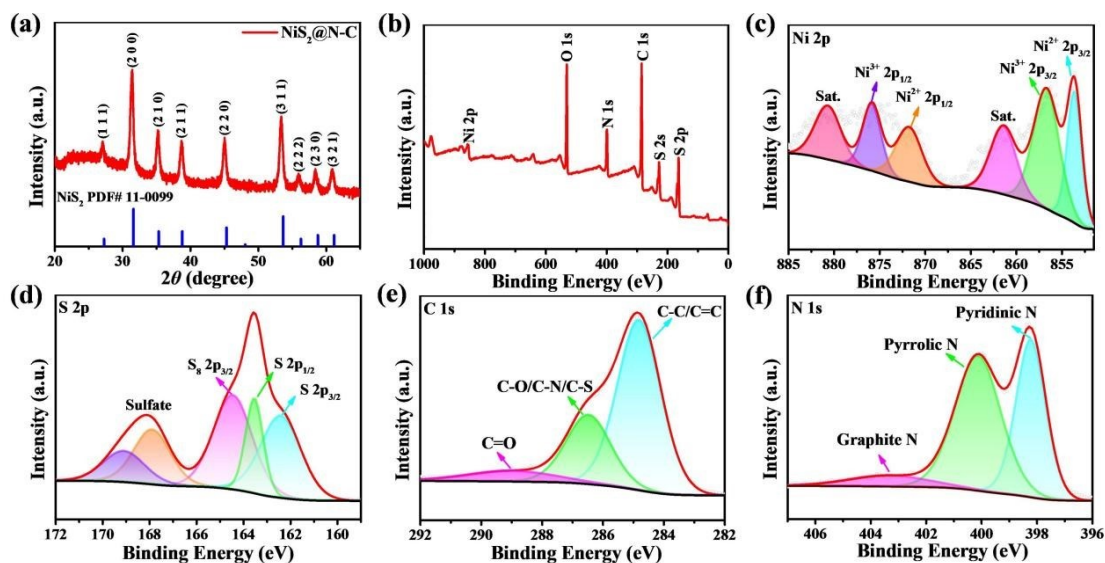


Figure S5. (a) XRD patterns of as-prepared NiS₂@N-C. (b) XPS survey spectrum of NiS₂@N-C. (c) Ni 2p. (d) S 2p. (e) C 1s. (f) N 1s spectra.

The high-resolution Ni 2p spectrum in Figure S5c reveals the orbital peaks corresponding to Ni²⁺ 2p_{1/2}, Ni²⁺ 2p_{3/2}, Ni³⁺ 2p_{1/2}, and Ni³⁺ 2p_{3/2} are observed at 871.88, 853.68, 875.88, and 856.78 eV, respectively. The presence of the Ni³⁺ may be attributed to the oxidation of some Ni²⁺ in the material to Ni³⁺. Furthermore, two typical satellites are observed at 861.48 and 880.78 eV.¹ For the S 2p spectrum of NiS₂@N-C shown in Figure S5d, the two primary peaks at 162.48 and 163.58 eV correspond to S 2p_{3/2} and S 2p_{1/2}, respectively, demonstrating the existence of the Ni—S bond.² Moreover, the peak at 164.48 eV is associated with the S—S bond of α-S₈, indicating the possible presence of residual S during the sulfurization process. The peaks at 168.4 and 169.5 eV are associated with S—O and sulfate bonds, respectively.³ In Figure S5e, the C 1s spectrum exhibits three distinct peaks at 284.78, 286.48, and 289.08 eV, corresponding to the C—C/C=C bond, the C—O/C—N/C—S bond, and the C=O bond, respectively. In Figure S5f, the observed peaks at 398.28, 399.98, and 403.38 eV in the N 1s spectrum can be attributed to three different nitrogen species: pyridinic N, pyrrolic N, and graphitic N, respectively.⁴ The nitrogen doping not only serves to increase the presence of defects, creating additional active sites for Na⁺ insertion, but also contributes to a further enhancement of the electrical conductivity within the carbon matrix.

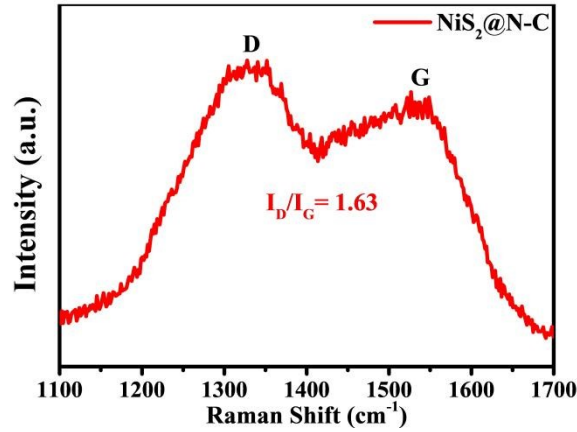


Figure S6. Raman spectrum of NiS₂@N-C.

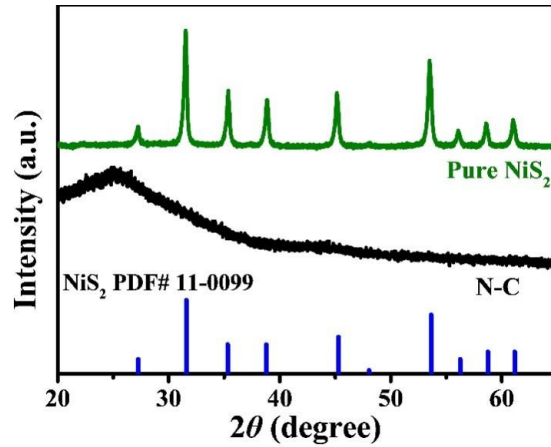


Figure S7. XRD patterns of Pure NiS₂ and N-C.

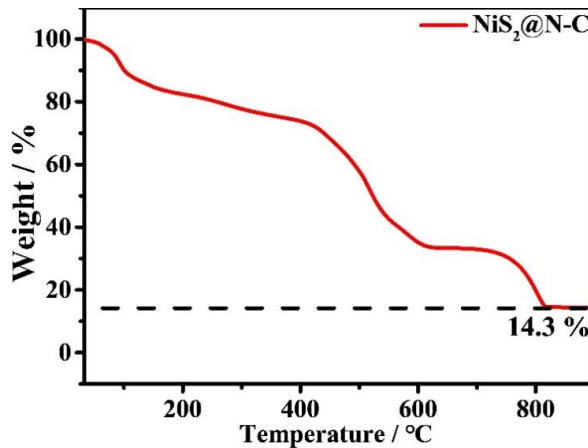


Figure S8. TGA analysis of NiS₂@N-C. Based on the follow equation:⁵ $2\text{NiS}_2(\text{s}) + \text{C}(\text{s}) + 6\text{O}_2(\text{g}) = 2\text{NiO}(\text{s}) + 4\text{SO}_2(\text{g}) + \text{CO}_2(\text{g})$. It can be inferred that only NiO was left after the TGA test, with a residual mass of 14.3% at 900 °C. Therefore, the content of NiS₂ can be calculated as follows: $14.3\% \times M_{\text{NiS}_2} \div M_{\text{NiO}} = 23.5\%$, and accordingly, the N-C content is determined to be 76.5%.

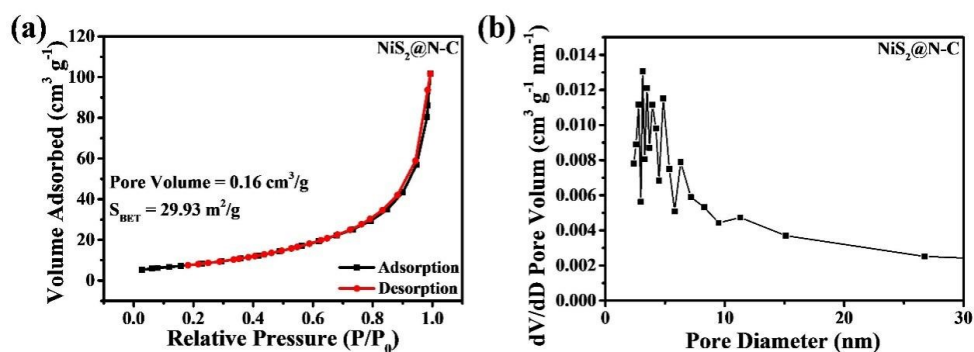


Figure S9. (a) The nitrogen adsorption–desorption isotherm, and (b) the corresponding pore size distribution of NiS₂@N-C.

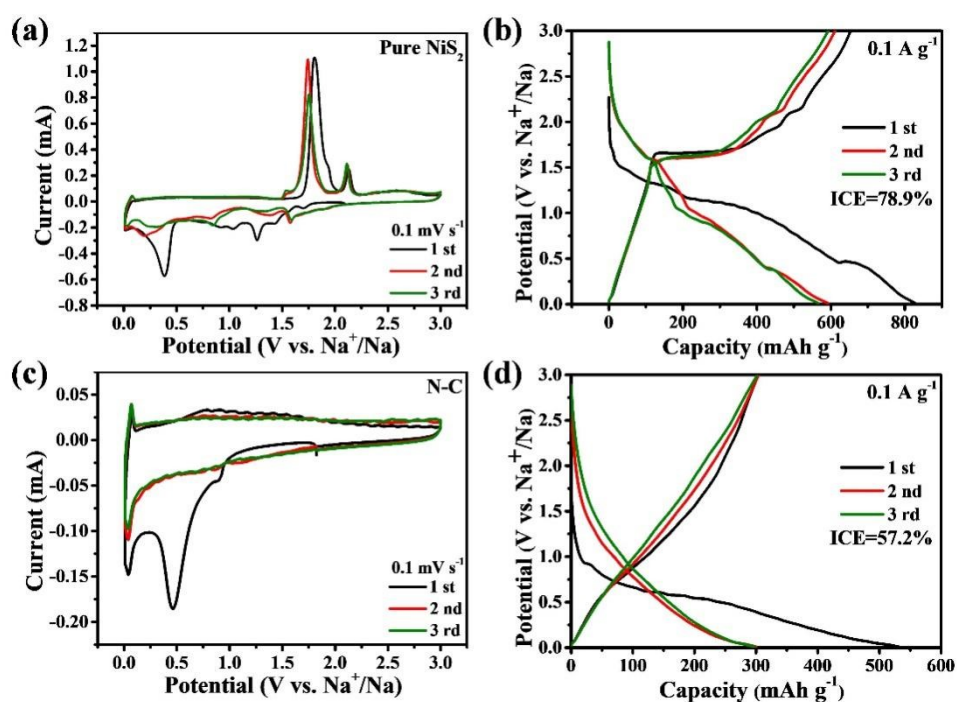


Figure S10. (a) CV curves of Pure NiS₂ at 0.1 mV s⁻¹ and (b) Charge and discharge curves of Pure NiS₂ at 0.1 A g⁻¹. (c) CV curves of N-C at 0.1 mV s⁻¹ and (d) Charge and discharge curves of N-C at 0.1 A g⁻¹.

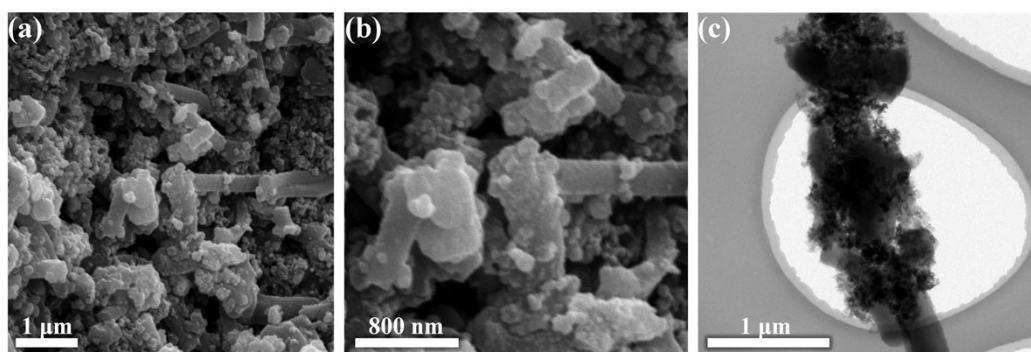


Figure S11. (a-b) SEM images, and (c) TEM images of NiS₂@N-C electrode after 900 cycles at a current density of 5 A g⁻¹.

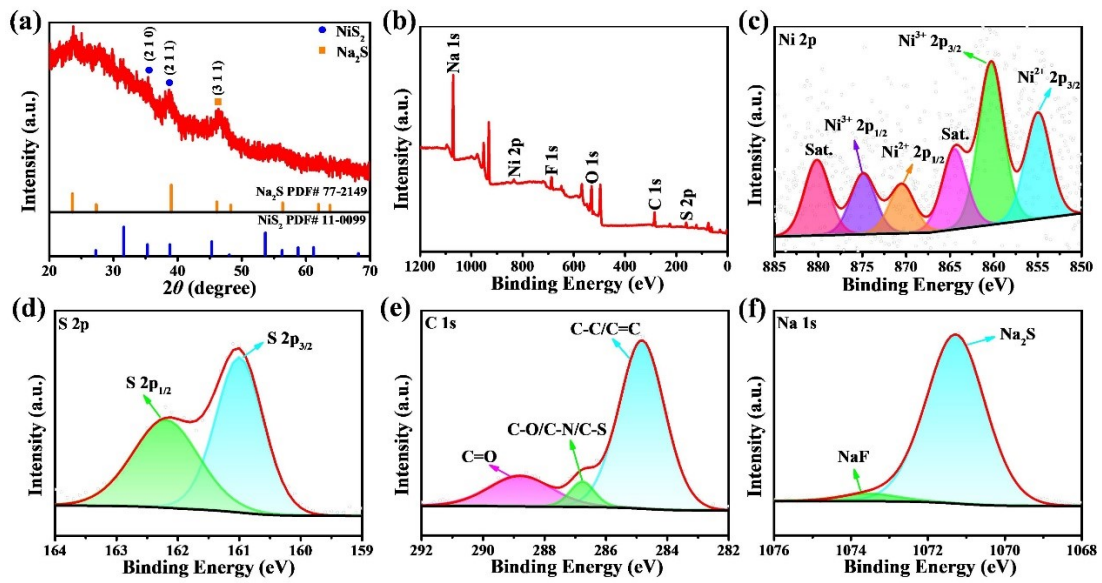


Figure S12. (a) XRD patterns of as-prepared NiS₂@N-C electrode after 900 cycles at a current density of 5 A g⁻¹. (b) XPS survey spectrum of NiS₂@N-C electrode after 900 cycles at a current density of 5 A g⁻¹. (c) Ni 2p. (d) S 2p. (e) C 1s. (f) Na 1s spectra.

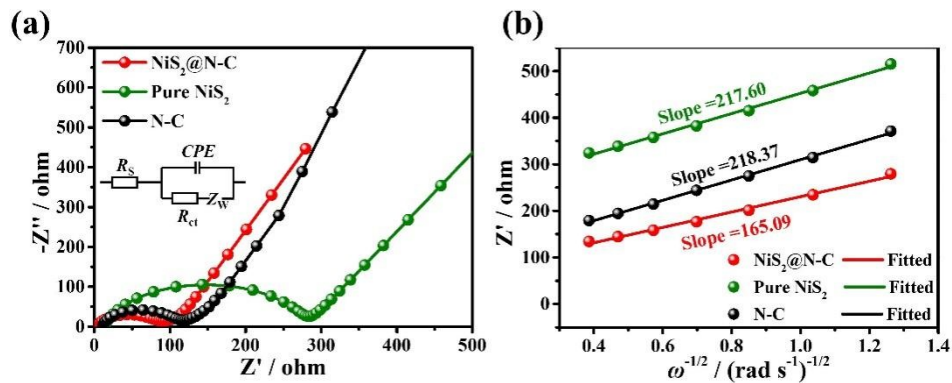


Figure S13. (a) EIS curves of different samples before cycling measurements and (b) the corresponding relationship between $\omega^{-1/2}$ and Z' in the low-frequency region.

The Nyquist plots obtained before cycling measurements are displayed in Figure S13a. The charge transfer resistance (R_{ct}) value of NiS₂@N-C (76.1 Ω) is significantly smaller than that of Pure NiS₂ (268.2 Ω) and N-C (92.2 Ω). This further indicates that the 3D conductive network of NiS₂@N-C significantly enhances electrical conductivity. Moreover, the Warburg factor σ is determined by plotting the slope of the fitted line of Z' versus $\omega^{-1/2}$, as depicted in Figure S13b. The diffusion coefficient of Na⁺ (D_{Na^+}) in the electrode material can be determined using the following formula:⁶

$$D_{Na^+} = \frac{R^2 T^2}{2n^4 F^4 S^2 C^2 \sigma^2}$$

Where R represents the gas constant, T denotes the absolute temperature, n represents the number

of electron transfers, F signifies the Faraday constant, S stands for the electrode surface area and C denotes the concentration of sodium ions in the electrolyte.

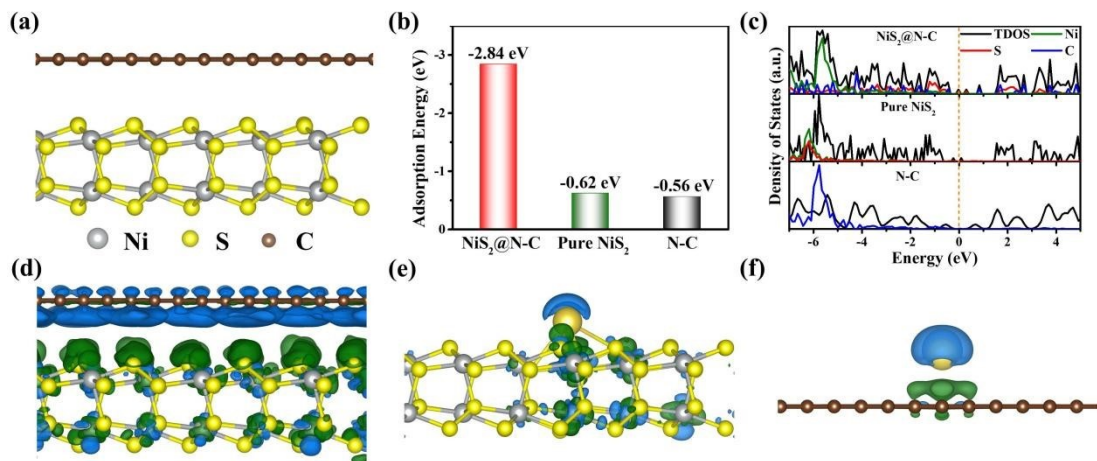


Figure S14. DFT calculations of three distinct models: (a) Structural model of NiS₂@N-C. (b) Sodium ion adsorption energies. (c) The DOS and (d-f) differential charge distribution map of NiS₂@N-C, Pure NiS₂ and N-C. The green part represents charge accumulation, and the blue region represents charge depletion.

Figure S14b presents the adsorption energies of NiS₂@N-C, Pure NiS₂ and N-C for Na⁺, which are -2.84 eV, -0.62 eV, and -0.56 eV, respectively. The results indicate that the adsorption energy of NiS₂@N-C for Na⁺ is significantly higher than that of Pure NiS₂@N-C and N-C, suggesting that NiS₂@N-C has a stronger affinity in the process of sodium ion adsorption. By calculating and analyzing the density of states (DOS) for three models (Figure S14c), we found that the heterostructure NiS₂@N-C exhibits a higher charge density near the Fermi level compared to both Pure NiS₂ and N-C, resulting in superior electrical conductivity. Furthermore, in Figure S14d, the differential charge density map of the NiS₂@N-C model illustrates the phenomenon of electron redistribution in the interface region (Figure S14e-f present the differential charge density map of Pure NiS₂ and N-C model, respectively). Specifically, a positive charge accumulation is observed on the NiS₂ side, while negative charge accumulation occurs on the N-C side. This charge redistribution arises from the interaction between NiS₂ and N-C. Notably, the polarity of the Ni–S bond facilitates electron transfer from Ni to S, and the conductivity of N-C promotes both migration and distribution of electrons.^{7, 8}

Table S1. Comparison of the performance of different NiS₂-based anode materials.

Materials	Potential range (V)	Rate performance		Cycling performance			Reference
		Current density (A g ⁻¹)	Capacity (mAh g ⁻¹)	Current density (A g ⁻¹)	Cycles	Retention (mAh g ⁻¹)	
NiS ₂ @N-C	0.01-3	5	444	1/5	300/900	585/486	This work
NiS ₂ @C@C	0.01-3	1.6	448	0.1	100	581	9
NiS ₂ @NC	0.005-3	3	294	0.1/0.5	100/300	506/356	10
Hollow NiS ₂ @G	0.005-3	2	528	1	300	530	11
MoS ₂ /NiS ₂	0.2-3	5	375	1	350	481	12
NiS ₂ /NG	0.01-2.6	2	545	0.5/2	1200/100	590/545	13
Ni@NCNTs HMs	0.2-3	5	333	1	500	345	2
NiS ₂	0.4-2.9	5	253	0.5	1000	319	14
NiS ₂ /Ti ₃ C ₂ T _x	0.01-3	2	147	1	800	179	15
NiS ₂ /rGO	0-3	10	320	5	500	308	16
ReS ₂ @NiS ₂	0-3	5	230	1	220	400	17
NiS ₂ @MWCNTs	0.01-3	2	382	0.2/1	400/600	464/419	18
NiS ₂ @rGO	0.2-2.8	5	324	1	1800	378	19
NiS ₂ NP/p-CNF	0.01-3	2	300	2	1000	200	20
NiS ₂ /N,S-rGO	0.01-3	1	205	0.1	200	208	21
CoS ₂ /NiS ₂ -RGO	0.01-3	0.5	58	0.1	200	127	22

References

- 1 B. Huang, J. Yuan, Y. Lu, Y. Zhao, X. Qian, H. Xu, G. He and H. Chen, *Chem. Eng. J.*, 2022, **436**, 135231.
- 2 B. Cong, X. Li and G. Chen, *Chem. Eng. J.*, 2023, **460**, 141713.
- 3 L. Lin, K. Wang, A. Sarkar, C. Njel, G. Karkera, Q. Wang, R. Azmi, M. Fichtner, H. Hahn, S. Schweidler and B. Breitung, *Adv. Energy Mater.*, 2022, **12**, 2103090.
- 4 Zulkifli, S. Lee, G. Alfaza, A. N. Fahri, B. Sambandam, V. Mathew, S. Lee, J. Park, M. Song, J. Lee, J. Y. Hwang and J. Kim, *Mate. Today Sustain.*, 2023, **22**, 100348.
- 5 S.-L. Yang, H.-B. Yao, M.-R. Gao and S.-H. Yu, *CrystEngComm*, 2009, **11**, 1383-1390.
- 6 P. Wang, J. Huang, J. Zhang, L. Wang, P. Sun, Y. Yang and Z. Yao, *J. Mater. Chem. A*, 2021, **9**, 7248-7256.
- 7 F. Chen, S. J. Robertson, X. Xu, S. Chen, C. Sun, M. Shao and J. Wang, *Nano Energy*, 2024, **123**, 109414.
- 8 F. He, X. Chen, Y. Xue and Y. Li, *Angew. Chem. Int. Ed. Engl.*, 2024, **63**, e202318080.
- 9 G. Zhao, Y. Zhang, L. Yang, Y. Jiang, Y. Zhang, W. Hong, Y. Tian, H. Zhao, J. Hu, L. Zhou, H. Hou, X. Ji and L. Mai, *Adv. Funct. Mater.*, 2018, **28**, 1803690.
- 10 J. Li, J. Li, D. Yan, S. Hou, X. Xu, T. Lu, Y. Yao, W. Mai and L. Pan, *J. Mater. Chem. A*, 2018, **6**, 6595-6605.
- 11 R. Bi, C. Zeng, H. Huang, X. Wang and L. Zhang, *J. Mater. Chem. A*, 2018, **6**, 14077-14082.
- 12 Y. Zhang, B. Han, Q. Gao, Z. Cai, C. Zhou, G. Hu, J. Li and R. Sun, *Nano Energy*, 2024, **128**, 109941.
- 13 S. Luo, J. Shang, Y. n. Xu, H. Cheng, L. Zhang and Y. Tang, *Adv. Funct. Mater.*, 2024, **34**, 2403166.
- 14 R. Sun, S. Liu, Q. Wei, J. Sheng, S. Zhu, Q. An and L. Mai, *Small*, 2017, **13**, 1701744.
- 15 W. X. Zhang, J. H. Zhang, Y. K. Zhang, C. He and P. Zhao, *Ionics*, 2022, **28**, 4621-4629.
- 16 H. Zheng, X. Chen, L. Li, C. Feng and S. Wang, *Mater. Res. Bull.*, 2021, **142**, 111430.
- 17 Z. Cai, Z. Peng, X. Liu, R. Sun, Z. Qin, H. Fan and Y. Zhang, *Chin. Chem. Lett.*, 2021, **32**, 3607-3612.
- 18 W. X. Zhang, Z. Li, J. H. Zhang, C. He and X. H. Ning, *J. Alloys Compd.*, 2024, **971**, 172669.
- 19 J. Cai, X. Chen, X. Duan, G. Yang, Q. Zhang, H. Fan, Z. Liu and F. Peng, *Electrochim. Acta*, 2023, **462**, 142705.
- 20 W. Zhao, S. Ci, X. Hu, J. Chen and Z. Wen, *Nanoscale*, 2019, **11**, 4688-4695.
- 21 X. Dong, F. Chen, G. Chen, B. Wang, X. Tian, X. Yan, Y. X. Yin, C. Deng, D. Wang, J. Mao, S. Xu and S. Zhang, *J. Colloid Interface Sci.*, 2022, **619**, 359-368.
- 22 J. Liu, Y.-G. Xu and L.-B. Kong, *J. Mater. Sci.: Mater. Electron.*, 2020, **31**, 9946-9959.